MM1101A/MM1101A1/ MM1101A2
256 Bit Fully Decoded Static Random Access Memory

REFERENCE TABLE

Code	Stock No.
MM1101AN	**34515F**
MM1101A1N	**34516D**
MM1101A2N	**34517B**

GENERAL DESCRIPTION

The MM1101 family of fully decoded 256 word × 1-bit random access memories are monolithic MOS integrated circuits using silicon gate low threshold technology to achieve bipolar compatibility. They are static, require no clocks, and hold information indefinitely, subject to the integrity of the power supply voltages.

APPLICATIONS

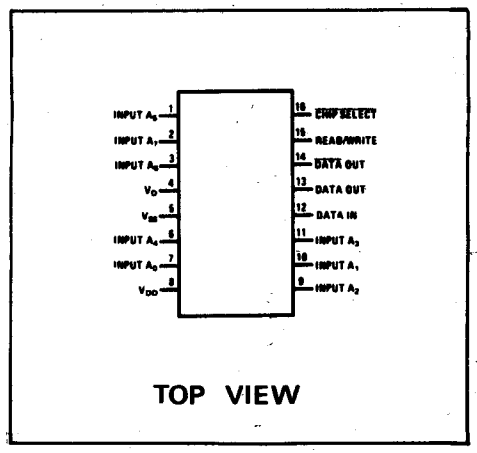
High speed buffer memories.

Local memory store.

ABSOLUTE MAXIMUM RATINGS

All input or output voltages with respect to the most positive supply V_{SS}	+0.3V to −20V
Supply voltages V_{DD} and V_D with respect to V_{SS}	−16V
Power dissipation	700mw
Operating temperature	0°C to 70°C
Storage temperature	−66°C to +160°C
Lead temperature (soldering 10 sec)	300°C

CONNECTION DIAGRAM



TOP VIEW

See outline drawing No. 111 for dimensions.

FEATURES

Fast access time MM1101A2 500ns max.

MM1101A1 1.0 μs max. MM1101, MM1101A 1.5 μs max.

Improved speed/power product MM1101A2 1/3 of 1101A.

Low power operation 1.5mW/bit

Fewer system components – bipolar compatible input and output.

Second source flexibility – MM1101, MM1101A, MM1101A1 second sources available.

TRI-STATE™ output – wired OR capability.

Specified ambient temperature 0°C to +70°C, for MM1101 family.